Crash Recovery Techniques for Flash Storage Devices L Review

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Citation Report

#	Article	IF	CITATIONS
1	Support Vector Regression Model for Determining Optimal Parameters of HfAlO-Based Charge Trapping Memory Devices. Electronics (Switzerland), 2023, 12, 3139.	3.1	0
2	An Effective Selection of Memory Technologies for TCAM to Improve the Search Operations: Demonstration of Memory Efficiency in SDN Recovery. Electronics (Switzerland), 2024, 13, 707.	3.1	O